

IN THE CLAIMS:

Please cancel claims 20-29 without prejudice and amend the claims as follows:

1. (Currently Amended) A nanoprobe, comprising:

a substrate having a layer formed thereon, the layer which forms forming a projected portion; and

a plurality of conductive lines adhered to the projected portion and further extending beyond an end of the projected portion by a distance to form contact points, wherein the lines are connected to material of the projected portion to provide stiffness and the contact points provide flexibility during use.

2. (Original) The nanoprobe as recited in claim 1, wherein the layer includes a dielectric layer and the dielectric layer forms the projected portion.

3. (Original) The nanoprobe as recited in claim 2, wherein the substrate includes silicon and the dielectric layer includes at least one of silicon nitride and silicon oxide.

4. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines include a thickness of between about 1% and about 10% of a thickness of the projected portion.

5. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines are formed from a noble metal.

6. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines are formed from one or more of Ag, Au, Pt, Ir, Ru, Pd and their alloys.

7. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines each have a thickness and a width, which are 300 nm, or less.

8. (Original) The nanoprobe as recited in claim 1, wherein the conductive lines include a pitch of less than or equal to one micron.

9. (Original) The nanoprobe as recited in claim 8, wherein the pitch is less than or equal to 600 nm.

10. (Original) The nanoprobe as recited in claim 1, wherein the nanoprobe includes circuitry formed thereon.

11. (Original) A nanoprobe for making electrical measurements, comprising:
a substrate;
a dielectric layer formed on the substrate and extending beyond an edge of the substrate to form a projected portion;
a plurality of conductive lines extending at least over the projected portion, the

conductive lines being adhered to the projected portion, the conductive lines further extending beyond an end of the projected portion by a distance to form contact points, wherein the lines are connected to the projected portion to provide stiffness and the contact points provide flexibility during use.

12. (Original) The nanoprobe as recited in claim 11, wherein the substrate includes silicon and the dielectric layer includes at least one of silicon nitride and silicon oxide.

13. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines include a thickness of between about 1% and about 10% of a thickness of the projected portion.

14. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines are formed from a noble metal.

15. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines are formed from one or more of Ag, Au, Pt, Ir, Ru, Pd and their alloys.

16. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines each have a thickness and a width, which are 300 nm, or less.

17. (Original) The nanoprobe as recited in claim 11, wherein the conductive lines include

a pitch of less than or equal to one micron.

18. (Original) The nanoprobe as recited in claim 17, wherein the pitch is less than or equal to 600 nm.

19. (Original) The nanoprobe as recited in claim 11, wherein the nanoprobe includes circuitry formed thereon.

Claims 20-29 (Canceled)